7-12 / 130 //	599	5 7	950	78
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SEARCH REQUEST FORM Scientific and Technical Information Center - EIC2800  This is an experimental format Please give suggestions or comments to Jeff Harrison, CP4-9C18, 306-5429.				
Date 5/27/03 Serial # 09/891,925 Priority Application Date 5/31/94				
Your Name Sara W. Crane Examiner # 64804				
AU 2811 Phone 703 308-4894 Room CPA 7A09				
In what format would you like your results? Paper is the default. PAPER DISK EMAIL				
If submitting more than one search, please prioritize in order of need.				
The EIC searcher normally will contact you before beginning a prior art search. If you would like to sit with a searcher for an interactive search, please notify one of the searchers.				
Where have you searched so far on this case?  O5-27-03 P03:16 IN  Circle: USPT DWPI EPO Abs (IBM TDB)				
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What relevant art have you found so far? Please attach pertinent citations or Information Disclosure Statements.				
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What is the topic, such as the <u>novelty</u> , motivation, utility, or other specific facets defining the				
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registry numbers, definitions, structures, strategies, and anything else that helps to describe the				
topic. Please attach a copy of the abstract and pertinent claims.				
I need a litigation search done for				
this reissue application. The priving of				
partent no. is 15945692 (Serial No.				
Date 10.				
08/432,812)				
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## STIC Database Tracking Number: 95078

TO: Sara Krane

Location: CP4- 4A09

**Art Unit: 2811** 

**Tuesday, May 27, 2003** 

Case Serial Number: 09/891925

From: Darcy Bates Location: EIC 2800

CP4-9C18

Phone: 306-5419

darcy.bates@uspto.gov

## Search Notes

Re: 09/891,925 US 5,945,692

Attached are search results.

No U. S. litigation was found in searches of Lexis-Nexis and Questel-Orbit databases.

If more searching or explanation is needed, please let me know.

Thanks, Darcy Bates



Source: Legal > Area of Law - By Topic > Patent Law > Patents > U.S. Patents > Utility Patents (i)

Terms: patno=5945692 (Edit Search)

432812 (08) 5945692 August 31, 1999

## UNITED STATES PATENT AND TRADEMARK OFFICE GRANTED PATENT **5945692**

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#### Link to Claims Section

August 31, 1999

Semiconductor device and method of fabricating same **REISSUE:** Reissue Application filed Jun. 27, 2001 (O.G. Sep. 11, 2001) Ex. Gp.: 2811; Re. S.N. 09/891,925, (O.G. September 11, 2001)

INVENTOR: Yano, Mitsuhiro, Fukuoka, JP; Mochizuki, Kouichi, Fukuoka, JP

**APPL-NO:** 432812 (08)

FILED-DATE: May 2, 1995

**GRANTED-DATE:** August 31, 1999

**PRIORITY:** May 31, 1994 - 6-118386 P, Japan (JP)

ASSIGNEE-AT-ISSUE: Mitsubishi Denki Kabushiki Kaisha, Tokyo, JP

**ASSIGNEE-AFTER-ISSUE:** June 14, 1995 - ASSIGNMENT OF ASSIGNORS INTEREST (SEE DOCUMENT FOR DETAILS)., MITSUBISHI DENKI KABUSHIKI KAISHA 2- 3, MARUNOUCHI 2-CHOME, CHIYODA-KU TOKYO J APAN 100, Reel and Frame Number: 007592/0717

**LEGAL-REP:** Oblon, Spivak, McClelland, Maier & Neustadt, P.C.

**PUB-TYPE:** August 31, 1999 - Utility Patent having no previously published pre-grant publication (A)

**PUB-COUNTRY:** United States (US)

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**US-ADDL-CL:** 257#212, 257#401, 257#630, 257#646, 257#649, 257#E29.011,

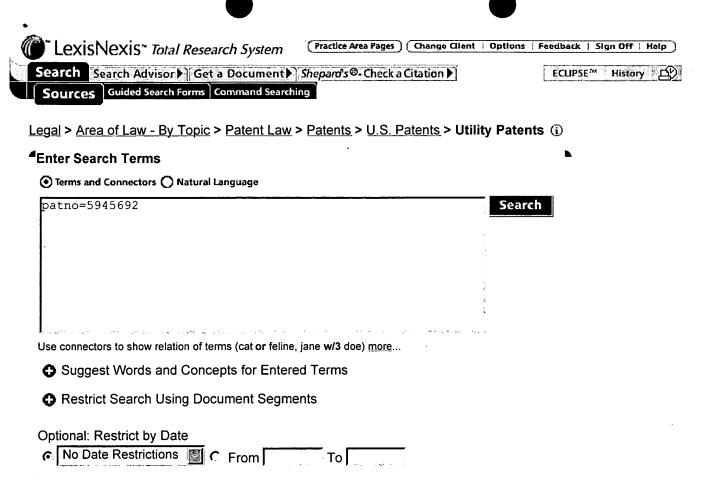
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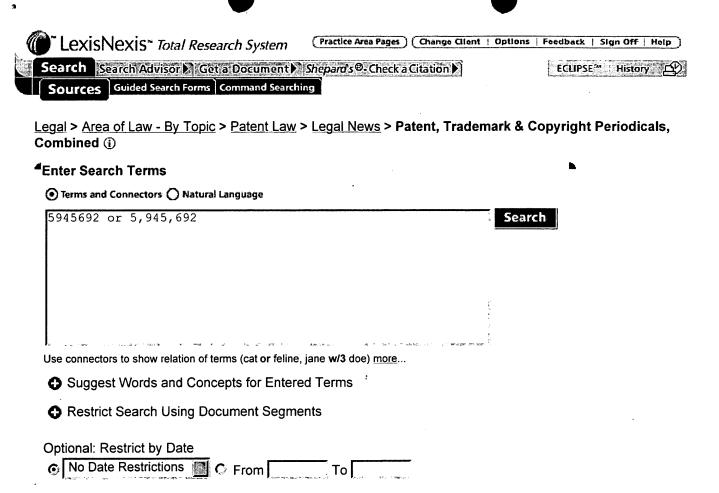
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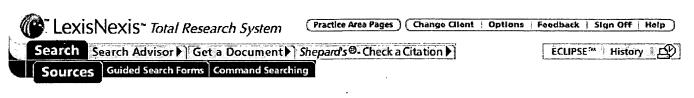
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Terms and Connectors					
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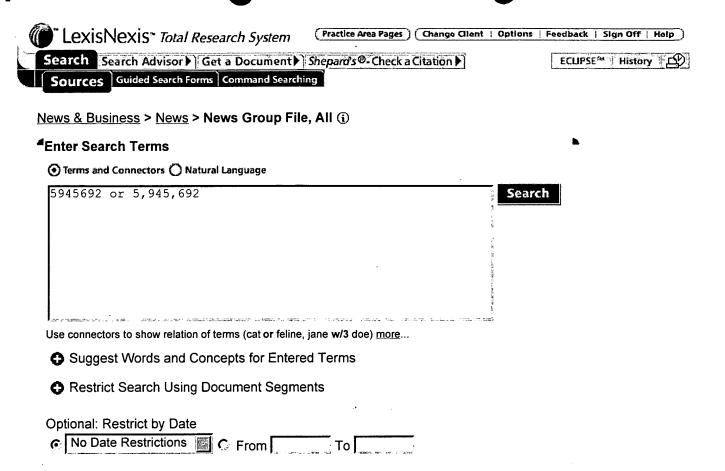
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Comprehensive Worldwide Patents database

New Patent Citation Commands & FAM Citation Report - see INFO PATCITE Last update of file: 2003/05/22 (YYYY/MM/DD) 2003-20/UP (basic update)

Search statement 1

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Search statement 2

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PN - US5945692 A 19990831 [US5945692]

TI - (A) Semiconductor device and method of fabricating same

PA - (A) MITSUBISHI ELECTRIC CORP (JP)

PAO - Mitsubishi Denki Kabushiki Kaisha, Tokyo [JP]

IN - (A) YANO MITSUHIRO (JP); MOCHIZUKI KOUICHI (JP)

AP - US43281295 19950502 [1995US-0432812]

PR - JP11838694 19940531 [1994JP-0118386]

IC - (A) H01L-029/74

EC - H01L-023/31

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- H01L-029/423D2B7C
- H01L-029/739C2
- H01L-029/78B2
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- DT Corresponding document
- CT US4161744; US4364073; US4814283; US5196354; US5521409; EP0091079; JP1-265524; JP4-57330; JP4-130631
  - Patent Abstracts of Japan, vol. 14, No. 408 (E-972) (4351), Sep. 4, 1990, and JP 2 153570, Jun. 13, 1990.

IEEE Transactions on Electron Devices, vol. ED-27, No. 2, pp. 340-343, Feb. 1980, Richard W. Coen, et al., "A High-Performance Planar Power Mosfet".

Patent Abstracts of Japan, vol. 11, No. 275 (E-537) (2722), Sep. 5, 1987, and JP 62 73766, Apr. 4, 1987.

Patent Abstracts of Japan, vol. 16, No. 558 (E-1294), Nov. 27, 1992, and JP 4 212468, Aug. 4, 1992.

STG - (A) United States patent

AB - There is disclosed a semiconductor device having an MOS gate for reducing variations in threshold voltage (Vth) with time wherein a surface protective film is not formed in a device area including channels but only in a device peripheral area, thereby reducing the amount of hydrogen atoms migrating to a silicon-silicon oxide interface in a cell area and, accordingly, reducing the number of Si--H chemical bonds at the interface.

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 ACT - 19950502 US/AE-A
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       MITSUBISHI DENKI KABUSHIKI KAISHA 2-3, MARUNOUCHI 2-CHOME, CHIYODA-KU
       TOKYO, JAP * YANO, MITSUHIRO: 19950411; MOCHIZUKI, KOUICHI: 19950411
     - 19990831 US/A
       PATENT
     - 20010911 US/RF
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 UP - 2001-40
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 PA - Mitsubishi Denki K K JP
 PT - E (Electrical)
 ACT - 20010627 REISSUE REQUESTED
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US 5,945,692

5/27/03

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IN - YANO MITSUHIRO [JP]; MOCHIZUKI KOUICHI [JP]
PA - MITSUBISHI ELECTRIC CORP [JP]
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TI - SEMICONDUCTOR DEVICE HAVING A MOS GATE STRUCTURE AND A SURFACE
     PROTECTIVE FILM AND METHOD OF FABRICATING THE SAME.
LA - ENG
IN - YANO MITSUHIRO C O MITSUBISHI [JP]; MOCHIZUKI KOUICHI C O FUKURYO [JP]
PA - MITSUBISHI ELECTRIC CORP [JP]
AP - EP 95107265/95-A 19950512 [1995EP-0107265]
PR - JP 118386/94-A 19940531 [1994JP-0118386]
IC - H01L-029/78; H01L-023/31; H01L-029/06; H01L-029/423; H01L-029/739
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TI - SEMICONDUCTOR DEVICE AND MANUFACTURE THEREOF
IN - YANO MITSUHIRO; MOCHIZUKI KOICHI
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TI - SEMICONDUCTOR DEVICE AND METHOD OF FABRICATING SAME
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PR - JP 118386/94-A 19940531 [1994JP-0118386]
IC - H01L-029/74
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